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Recitation 3 : Bipolar junction transistor (BJT) Static Study

Exercise 1

We consider a bipolar transistor powered by a voltage source E=30V. The two circuits which will be successively associated with it must impose a collector current IC of 10mA. We specify that the current gain β =350 and VBE=0.6V.



1. Consider the circuit of Figure 1

1.1. Determine the values of RC and RB in which the operating point is located in the middle of the static load line.

2. The circuit in Figure 2 is mixed biasing made using a base bridge and a resistor on the emitter RE=100 Ω .

Note: The current IB is negligible compared to the current passing through RB1 and RB2.

2.1. What must be the values of RB1 and RB2 of the base bridge in which the collector current is still 10mA, knowing that RB=RB1 //RB2=10K Ω . The RC resistance has the value found previously.

Exercise 2

Consider the circuit based on a bipolar transistor (Q1) given in the figure below:





1. Calculate the value of the resistors R_E , R_1 et R_2 as well as RB=R1//R2.

Homework

For the circuit in the Figure 4, find VB, VE and VC for RB=100K Ω , 10K Ω , and 1K Ω . Let β =100 Ω .

